

# TIP31, TIP31A, TIP31B, TIP31C, (NPN), TIP32, TIP32A, TIP32B, TIP32C, (PNP)



ON Semiconductor®

<http://onsemi.com>

## Complementary Silicon Plastic Power Transistors

Designed for use in general purpose amplifier and switching applications.

### Features

- Collector–Emitter Saturation Voltage –  
 $V_{CE(sat)} = 1.2 \text{ Vdc (Max) @ } I_C = 3.0 \text{ Adc}$
- Collector–Emitter Sustaining Voltage –  
 $V_{CEO(sus)} = 40 \text{ Vdc (Min) – TIP31, TIP32}$   
 $= 60 \text{ Vdc (Min) – TIP31A, TIP32A}$   
 $= 80 \text{ Vdc (Min) – TIP31B, TIP32B}$   
 $= 100 \text{ Vdc (Min) – TIP31C, TIP32C}$
- High Current Gain – Bandwidth Product  
 $f_T = 3.0 \text{ MHz (Min) @ } I_C = 500 \text{ mAdc}$
- Compact TO–220 AB Package
- Pb–Free Packages are Available\*

### MAXIMUM RATINGS

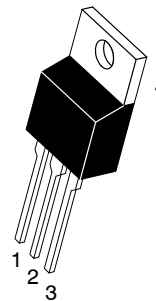
Rating	Symbol	Value	Unit
Collector – Emitter Voltage TIP31, TIP32 TIP31A, TIP32A TIP31B, TIP32B TIP31C, TIP32C	$V_{CEO}$	40 60 80 100	Vdc
Collector–Base Voltage TIP31, TIP32 TIP31A, TIP32A TIP31B, TIP32B TIP31C, TIP32C	$V_{CB}$	40 60 80 100	Vdc
Emitter–Base Voltage	$V_{EB}$	5.0	Vdc
Collector Current Continuous Peak	$I_C$	3.0 5.0	Adc
Base Current	$I_B$	1.0	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	40 0.32	W W/°C
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	2.0 0.016	W W/°C
Unclamped Inductive Load Energy (Note 1)	E	32	mJ
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	–65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1.  $I_C = 1.8 \text{ A}$ ,  $L = 20 \text{ mH}$ , P.R.F. = 10 Hz,  $V_{CC} = 10 \text{ V}$ ,  $R_{BE} = 100 \Omega$

\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## 3 AMPERE POWER TRANSISTORS COMPLEMENTARY SILICON 40–60–80–100 VOLTS, 40 WATTS



TO–220AB  
CASE 221A  
STYLE 1

PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

### MARKING DIAGRAM



TIP3xx = Device Code  
xx = 1, 1A, 1B, 1C,  
2, 2A, 2B, 2C,  
A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb–Free Package

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

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## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.125	°C/W

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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## OFF CHARACTERISTICS

Collector-Emitter Sustaining Voltage (Note 2) ( $I_C = 30 \text{ mAdc}$ , $I_B = 0$ )	TIP31, TIP32 TIP31A, TIP32A TIP31B, TIP32B TIP31C, TIP32C	$V_{CE(sus)}$	40 60 80 100	- - - -	Vdc
Collector Cutoff Current ( $V_{CE} = 30 \text{ Vdc}$ , $I_B = 0$ ) ( $V_{CE} = 60 \text{ Vdc}$ , $I_B = 0$ )	TIP31, TIP32, TIP31A, TIP32A TIP31B, TIP31C, TIP32B, TIP32C	$I_{CEO}$	- -	0.3 0.3	mAdc
Collector Cutoff Current ( $V_{CE} = 40 \text{ Vdc}$ , $V_{EB} = 0$ ) ( $V_{CE} = 60 \text{ Vdc}$ , $V_{EB} = 0$ ) ( $V_{CE} = 80 \text{ Vdc}$ , $V_{EB} = 0$ ) ( $V_{CE} = 100 \text{ Vdc}$ , $V_{EB} = 0$ )	TIP31, TIP32 TIP31A, TIP32A TIP31B, TIP32B TIP31C, TIP32C	$I_{CES}$	- - - -	200 200 200 200	$\mu\text{Adc}$
Emitter Cutoff Current ( $V_{BE} = 5.0 \text{ Vdc}$ , $I_C = 0$ )		$I_{EBO}$	-	1.0	mAdc

## ON CHARACTERISTICS (Note 2)

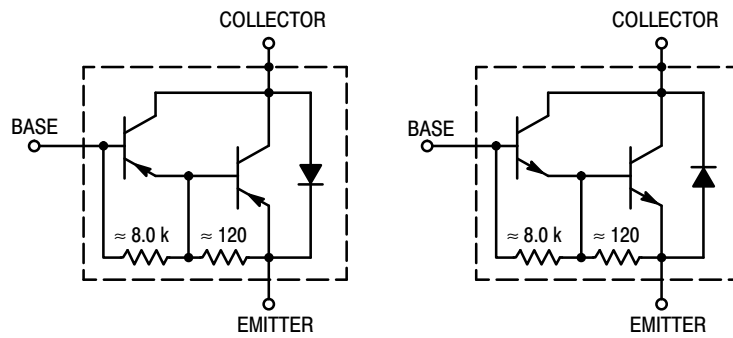
DC Current Gain ( $I_C = 1.0 \text{ Adc}$ , $V_{CE} = 4.0 \text{ Vdc}$ ) ( $I_C = 3.0 \text{ Adc}$ , $V_{CE} = 4.0 \text{ Vdc}$ )		$h_{FE}$	25 10	- 50	-
Collector-Emitter Saturation Voltage ( $I_C = 3.0 \text{ Adc}$ , $I_B = 375 \text{ mAdc}$ )		$V_{CE(sat)}$	-	1.2	Vdc
Base-Emitter On Voltage ( $I_C = 3.0 \text{ Adc}$ , $V_{CE} = 4.0 \text{ Vdc}$ )		$V_{BE(on)}$	-	1.8	Vdc

## DYNAMIC CHARACTERISTICS

Current-Gain – Bandwidth Product ( $I_C = 500 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f_{test} = 1.0 \text{ MHz}$ )		$f_T$	3.0	-	MHz
Small-Signal Current Gain ( $I_C = 0.5 \text{ Adc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 1.0 \text{ kHz}$ )		$h_{fe}$	20	-	-

2. Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

**TIP31, TIP31A, TIP31B, TIP31C, (NPN), TIP32, TIP32A, TIP32B, TIP32C, (PNP)**



**Figure 1. Darlington Circuit Schematic**

**ORDERING INFORMATION**

Device	Package	Shipping
TIP31	TO-220	50 Units / Rail
TIP31G	TO-220 (Pb-Free)	50 Units / Rail
TIP31A	TO-220	50 Units / Rail
TIP31AG	TO-220 (Pb-Free)	50 Units / Rail
TIP31B	TO-220	50 Units / Rail
TIP31BG	TO-220 (Pb-Free)	50 Units / Rail
TIP31C	TO-220	50 Units / Rail
TIP31CG	TO-220 (Pb-Free)	50 Units / Rail
TIP32	TO-220	50 Units / Rail
TIP32G	TO-220 (Pb-Free)	50 Units / Rail
TIP32A	TO-220	50 Units / Rail
TIP32AG	TO-220 (Pb-Free)	50 Units / Rail
TIP32B	TO-220	50 Units / Rail
TIP32BG	TO-220 (Pb-Free)	50 Units / Rail
TIP32C	TO-220	50 Units / Rail
TIP32CG	TO-220 (Pb-Free)	50 Units / Rail

TIP31, TIP31A, TIP31B, TIP31C, (NPN), TIP32, TIP32A, TIP32B, TIP32C, (PNP)

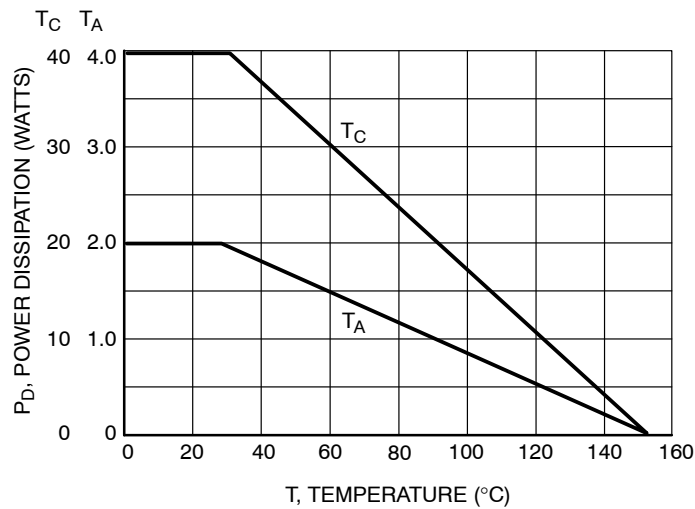
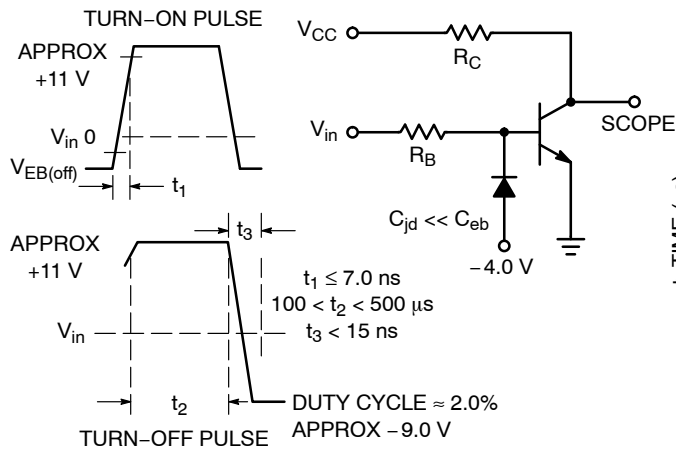


Figure 2. Power Derating



$R_B$  and  $R_C$  VARIED TO OBTAIN DESIRED CURRENT LEVELS.

Figure 3. Switching Time Equivalent Circuit

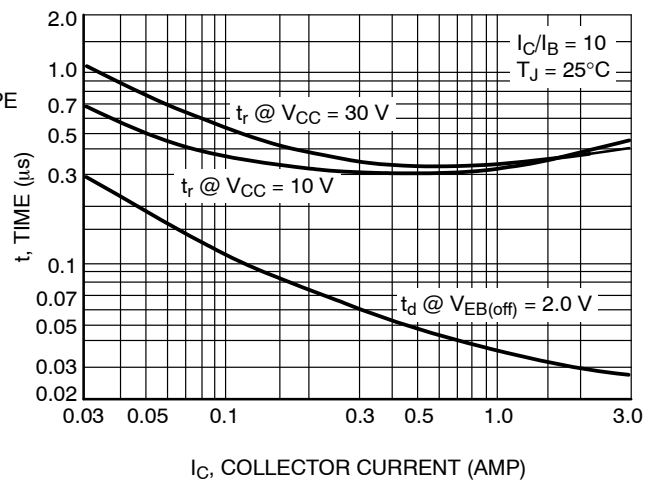


Figure 4. Turn-On Time

TIP31, TIP31A, TIP31B, TIP31C, (NPN), TIP32, TIP32A, TIP32B, TIP32C, (PNP)

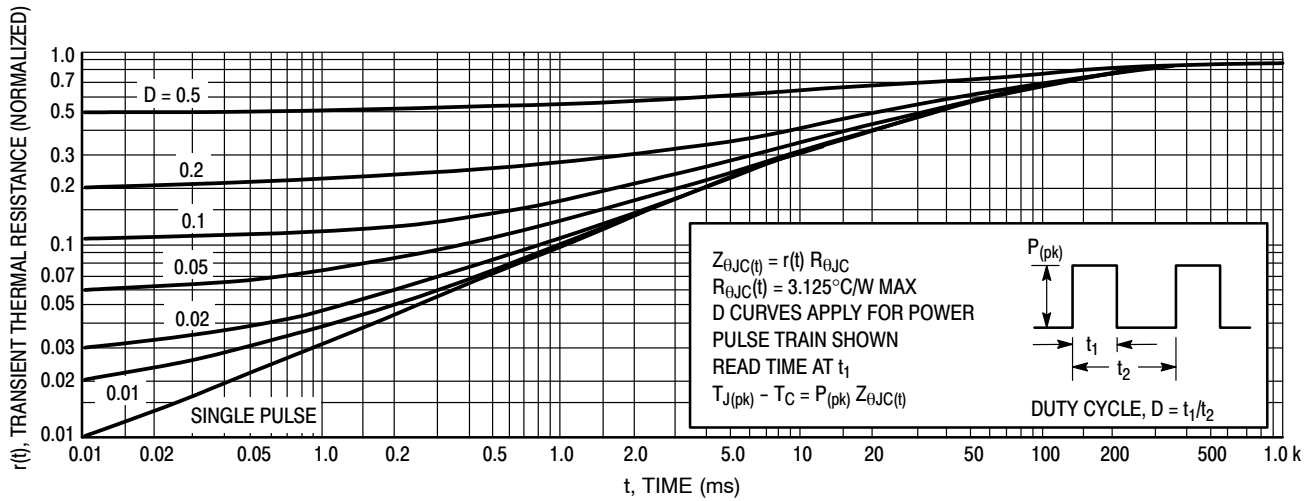


Figure 5. Thermal Response



Figure 6. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.



Figure 7. Turn-Off Time



Figure 8. Capacitance

TIP31, TIP31A, TIP31B, TIP31C, (NPN), TIP32, TIP32A, TIP32B, TIP32C, (PNP)

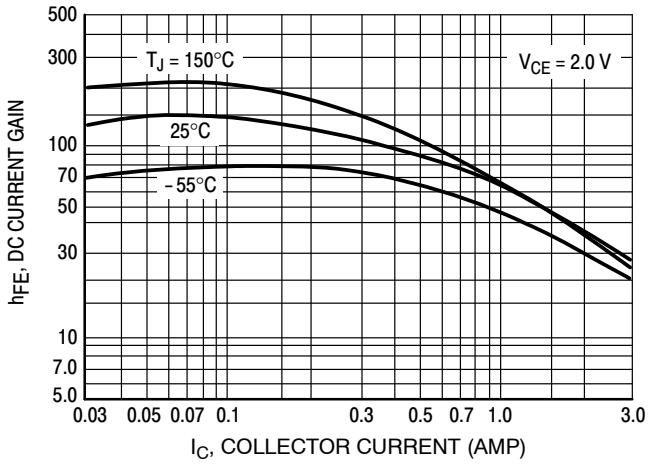


Figure 9. DC Current Gain

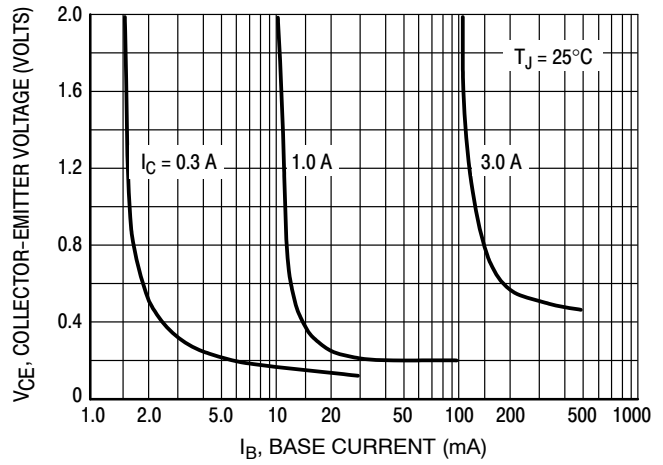


Figure 10. Collector Saturation Region

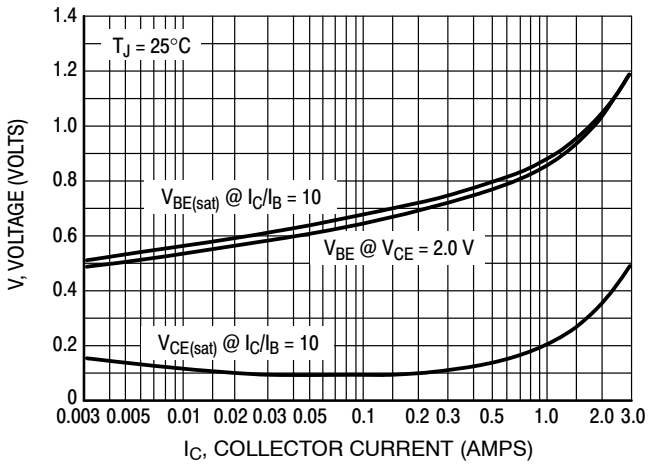


Figure 11. "On" Voltages

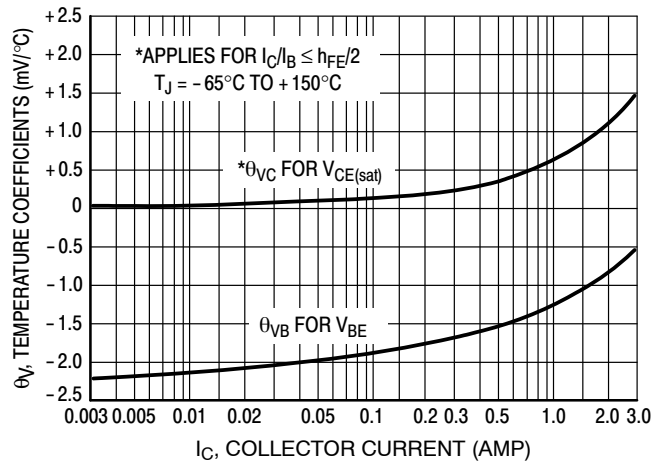


Figure 12. Temperature Coefficients

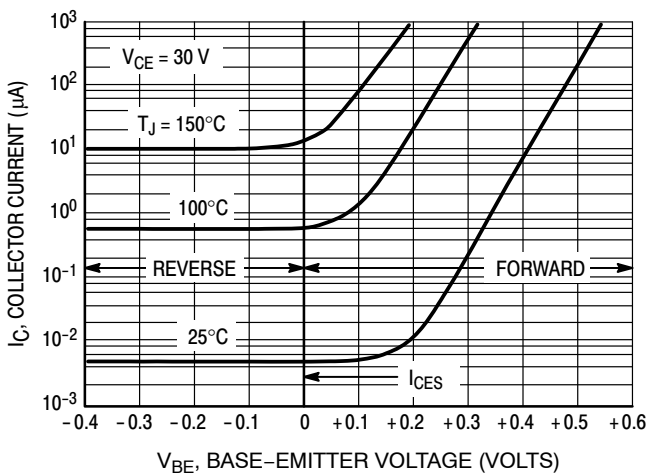


Figure 13. Collector Cut-Off Region

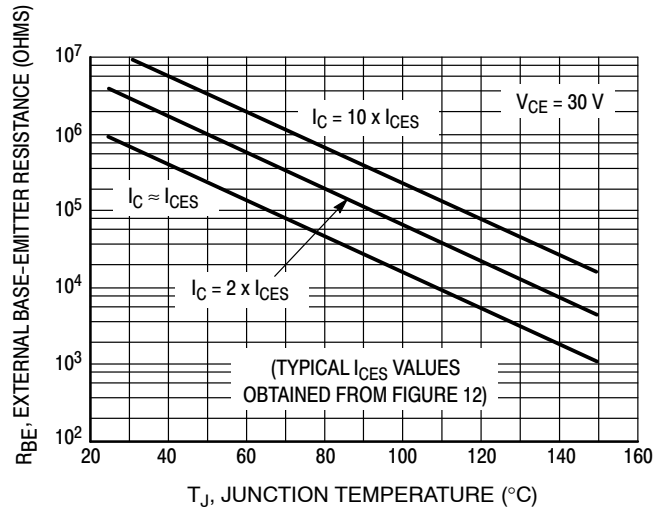
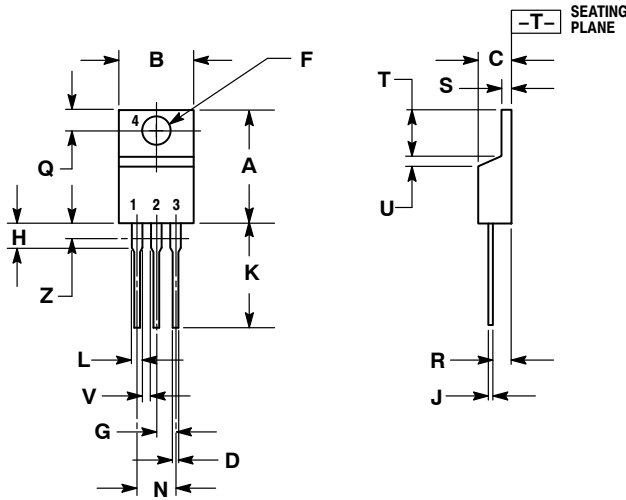


Figure 14. Effects of Base-Emitter Resistance

# TIP31, TIP31A, TIP31B, TIP31C, (NPN), TIP32, TIP32A, TIP32B, TIP32C, (PNP)

## PACKAGE DIMENSIONS

### TO-220 CASE 221A-09 ISSUE AG



#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.036	0.64	0.91
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

#### STYLE 1:

- PIN 1. BASE
- COLLECTOR
- EMITTER
- COLLECTOR

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- Техническая поддержка проекта;
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**Телефон:** 8 (812) 309 58 32 (многоканальный)

**Факс:** 8 (812) 320-02-42

**Электронная почта:** [org@eplast1.ru](mailto:org@eplast1.ru)

**Адрес:** 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.